

Title (en)
Semiconductor integrated circuit.

Title (de)
Integrierte Halbleiterschaltung.

Title (fr)
Circuit intégré semi-conducteur.

Publication
EP 0410473 B1 19951115 (EN)

Application
EP 90114459 A 19900727

Priority
JP 19595189 A 19890728

Abstract (en)
[origin: EP0410473A2] There is disclosed a semiconductor integrated circuit provided with an input circuit including an N-channel MOS transistor (N2) of which threshold voltage is set to a value lower than those of N-channel MOS transistors (N1, N3, N4) constituting other internal circuits of the integrated circuit. Thus, a circuit having a high operating margin for power supply noises is provided. This circuit further comprises a P-channel MOS transistor (P2) constituting a portion of a NOR gate or a NAND gate together with the above-mentioned N-channel MOS transistor (N2).

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H03K 19/003

IPC 8 full level
H03K 19/003 (2006.01); **H03K 19/0185** (2006.01); **H03K 19/0948** (2006.01)

CPC (source: EP KR US)
H03K 19/00 (2013.01 - KR); **H03K 19/00361** (2013.01 - EP US); **H03K 19/00384** (2013.01 - EP US)

Cited by
DE4336720B4; GB2304244A; GB2304244B

Designated contracting state (EPC)
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EP 0410473 A2 19910130; EP 0410473 A3 19910731; EP 0410473 B1 19951115; DE 69023565 D1 19951221; DE 69023565 T2 19960502; JP H0360218 A 19910315; JP H07114359 B2 19951206; KR 910003940 A 19910228; KR 930003926 B1 19930515; US 5073726 A 19911217

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